

2N681 thru 2N689 (SILICON)

CASE 263



Industrial-type, silicon controlled rectifiers in a stud package with current handling capability to 25 amperes at junction temperatures to 125°C. MCR equivalents available in TO-48 package — i.e. — 2N681 available in TO-48 package as MCR681.

MAXIMUM RATINGS ($T_J = 125^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Reverse Blocking Voltage* †	$V_{RSM}(\text{rep})^*$ †		
2N681		25	
2N682		50	
2N683		100	
2N684		150	
2N685		200	
2N686		250	
2N687		300	
2N688		400	
2N689		500	
Peak Reverse Blocking Voltage* (Transient) (non-recurrent $t = 5 \text{ ms}$ max.)	$V_{RSM}(\text{non-rep})^*$		Volts
2N681		35	
2N682		75	
2N683		150	
2N684		225	
2N685		300	
2N686		350	
2N687		400	
2N688		500	
2N689		600	
Forward Current RMS (all conduction angles)	I_T	25	Amp
Peak Forward Surge Current (One cycle, 60 Hz, $T_J = -65$ to $+125^\circ\text{C}$)	I_{TSM}	200	Amp
Circuit Fusing Considerations ($T_J = -65$ to $+125^\circ\text{C}$, $t \leq 8.3 \text{ ms}$)	I^2t	165	A^2s
Peak Gate Power-Forward	P_{GM}	5.0	Watts
Average Gate Power-Forward	$P_{G(AV)}$	0.5	Watt
Peak Gate Current-Forward	I_{GM}	2.0	Amp
Peak Gate Voltage-Forward Reverse	V_{GFM} V_{GRM}	10 5.0	Volts
Operating Junction Temperature Range	T_J	-65 to $+125$	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to $+150$	$^\circ\text{C}$
Stud Torque	—	30	in. lb.

* V_{RSM} for all types can be applied on a continuous dc basis without incurring change.

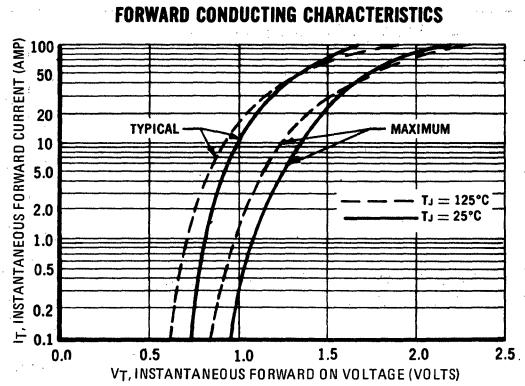
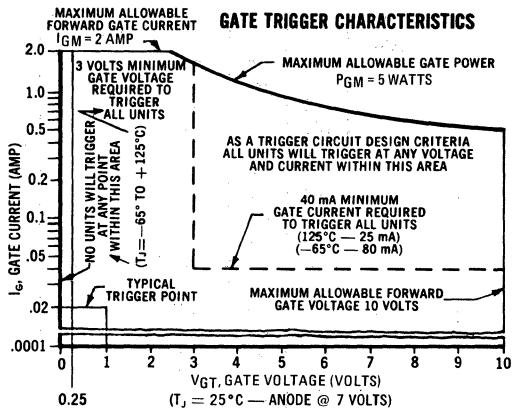
* $V_{RSM}(\text{rep})$ ratings apply for zero or negative gate voltage.

2N681 thru 2N689 (continued)

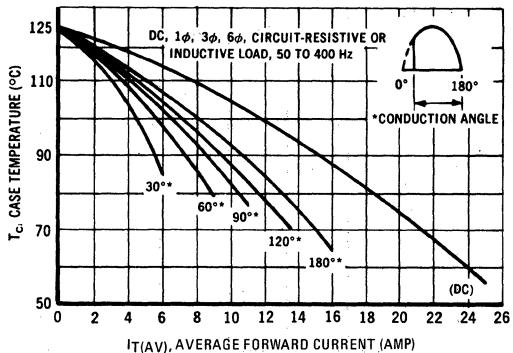
ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Units
Peak Forward Blocking Voltage ($T_J = 125^\circ\text{C}$) 2N681 2N682 2N683 2N684 2N685 2N686 2N687 2N688 2N689	V_{DRM}	25 50 100 150 200 250 300 400 500	— — — — — — — — —	— — — — — — — — —	Volts
Peak Forward or Reverse Blocking Current ($T_J = 125^\circ\text{C}$) 2N681 - 2N684 2N685 2N686 2N687 2N688 2N689	I_{DRM} I_{RRM}	— — — — — —	— — — — — —	10.0 10.0 10.0 10.0 8.0 6.0	mA
Gate Trigger Current (Continuous dc) (Anode Voltage = 7 Vdc, $R_L = 50 \Omega$)	I_{GT}	—	10	25	mA
Gate Trigger Voltage (Continuous dc) (Anode Voltage = 7 Vdc, $R_L = 50 \Omega$)	V_{GT}	0.25	—	3.0	Volts
Holding Current (Anode Voltage = 7 Vdc, Gate Open)	I_H	—	20	—	mA
Forward On Voltage ($I_T = 20 \text{ Adc}$)	V_{TM}	—	1.1	1.5	Volts
Turn-On Time ($I_T = 10\text{A}$, $I_G = 200 \text{ mA}$)	t_{gt}	—	1.0	—	μs
Turn-Off Time ($I_T = 10 \text{ A}$; $I_R = 10 \text{ A}$, $dv/dt = 30 \text{ V}/\mu\text{s}$ min, $T_J = 125^\circ\text{C}$) ($V_{DRM} = \text{rated voltage}$)	t_q	—	30	—	μs
Forward Voltage Application Rate (Gate open, $T_J = 125^\circ\text{C}$)	dv/dt	—	30	—	$\text{V}/\mu\text{s}$
Thermal Resistance (Junction to Case)	θ_{JC}	—	1.0	2.0	$^\circ\text{C}/\text{W}$

2N681 thru 2N689 (continued)



CURRENT DERATING



SUGGESTED FIN SIZES

